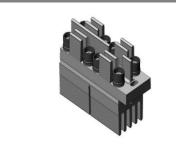
## **SKKQ 560**



SEMiSTART

# Antiparallel thyristors for softstart

#### **SKKQ 560**

Preliminary Data

#### Features

- Compact design
- Thyristor with amplifying gate
- Pressure contact technology

### **Typical Applications**

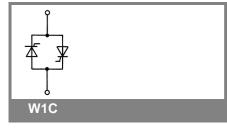
Soft Starters

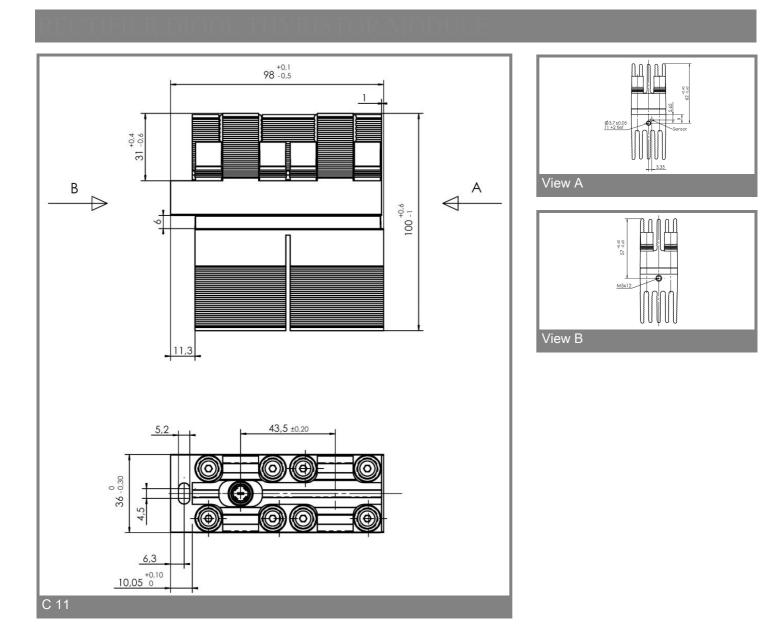
#### Remarks

- Please note: This module has no soft mold protection around the chip. It is therefore susceptible to environmental influences (dust, humidity, etc.). The humidity test according to IEC60068-2-67 is not passed by this product.
- T<sub>vjmax</sub> up to 150°C is allowable for overload conditions, max. time period for the overload condition is 20s.

Absolute Maximum Ratings							
Symbol	Conditions	Values	Units				
I <sub>overload</sub>	W1C; sin. 180°; 20 sec.; T <sub>vimax.</sub> = 150 °C; T <sub>vistart</sub> = 40°C	560	А				
I <sub>TSM</sub>	T <sub>vi</sub> = 25°C; 10 ms	5700	А				
	T <sub>vi</sub> = 125°C; 10 ms	5200	Α				
l²t	T <sub>vi</sub> = 25°C; 8,3 10 ms	162000	A²s				
	T <sub>vj</sub> = 125°C; 8,3 10 ms	135000	A²s				
SKKQ 560/14							
V <sub>RSM</sub>		1500	V				
$V_{RRM}, V_{DRM}$		1400	V				
SKKQ 560/18							
V <sub>RSM</sub>		1900	V				
V <sub>RRM</sub> ,V <sub>DRM</sub>		1800	V				
T <sub>vj</sub>		-40 +125 <sup>1)</sup>	°C				
T <sub>stg</sub>		-40 +125	°C				
		•					

Characteristics						
Symbol	Conditions	min.	typ.	max.	Units	
V <sub>T</sub>	T <sub>vi</sub> = 25°C; I <sub>T</sub> = 1000 A			1,9	V	
V <sub>T(TO)</sub>	$T_{v_i} = 125^{\circ}C$			0,9	V	
r <sub>T</sub>	$T_{vj} = 125^{\circ}C$			0,9	mΩ	
I <sub>DD</sub> ;I <sub>RD</sub>	$T_{vj}$ = 125°C; $V_{RD}$ = $V_{RRM}$ ; per module			60	mA	
t <sub>gd</sub>	$T_{vj} = 25^{\circ}C; I_{G} = 1A; di_{G}/dt = 1A/\mu s$		1		μs	
t <sub>gr</sub>	V <sub>D</sub> = 0,67 * V <sub>DRM</sub>		2		μs	
(dv/dt) <sub>cr</sub>	T <sub>vi</sub> = 125°C		1000		V/µs	
(di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125°C; f = 50 60 Hz		125		A/µs	
t <sub>q</sub>	T <sub>vi</sub> = 125°C		150		μs	
Ι <sub>H</sub>	$T_{vj} = 25^{\circ}C$		150	400	mA	
I <sub>L</sub>	T <sub>vj</sub> = 25°C; R <sub>G</sub> = 33 Ω		300	1000	mA	
V <sub>GT</sub>	T <sub>vi</sub> = 25°C; d.c.	2			V	
I <sub>GT</sub>	T <sub>vi</sub> = 25°C; d.c.	150			mA	
V <sub>GD</sub>	T <sub>vj</sub> = 125°C; d.c.			0,25	V	
I <sub>GD</sub>	$T_{vj} = 125^{\circ}C; d.c.$			10	mA	
R <sub>th(j-s)</sub>	cont.; per thyristor			0,106	K/W	
M <sub>t</sub>			5 ± 15%		Nm	
m			530		g	
Case			C 11			





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